NSN 5961-01-050-4828

Transistor - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-050-4828 **Inclosure Material:** Glass and metal **Overall Length:** 0.450 inches **Overall Diameter:** 0.875 inches **Mounting Facility Quantity:** 2 **Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-3 **Electrode Internally-electrically Connected To Case:** Collector **Internal Junction Configuration:** Npn **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 100.0 breakdown voltage, collector-to-base, emitter open and 7.0 breakdown voltage, emitter-to-base, collector open and 60.0 breakdown voltage, collector-to-emitter, base open **Current Rating Per Characteristic:** 20.00 amperes source cutoff current and 5.00 amperes source cutoff current **Power Rating Per Characteristic:** 150.0 watts small-signal input power, common-collector **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Terminal Type And Quantity:** 1 case and 2 pin Shelf Life: N/a **Unit Of Measure: Demilitarization:** No

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